CLAIMS

I claim:

- 1. An assembly for packaging and cooling a semiconductor die comprising:
 - a substrate;
 - a semiconductor die mounted on the substrate;
- a thermal spreader in heat conducting relation with the semiconductor die on a side of the die opposite the substrate; and
- a gasket of a lossy material on the substrate surrounding the die to protect the die from electrostatic discharge pulses.
- 2. The assembly according to claim 1, wherein the thermal spreader extends beyond the outer peripheral edge of the die and overhangs an adjacent edge of the gasket.
- 3. The assembly according to claim 1, further comprising a heat sink in heat conducting relation with the thermal spreader on a side of the thermal spreader opposite the die.

- 4. The assembly according to claim 1, wherein the semiconductor die is a microprocessor.
- 5. The assembly according to claim 1, wherein the lossy material of the gasket is a static dissipative material having a volume resistivity of greater than 10^2 ohm cm.
- 6. The assembly according to claim 5, wherein the volume resistivity of the static dissipative material is less than 10⁹ ohm cm.
- 7. The assembly according to claim 1, wherein the gasket is bonded to the substrate with an adhesive.
- 8. The assembly according to claim 7, wherein the adhesive is conductive.
- 9. The assembly according to claim 1, wherein the gasket is formed of expanded polytetrafluorethylene material filled with a conductive material to the

extent that the gasket material has a volume resistivity of greater than 10² ohm cm.

- 10. The assembly according to claim 1, wherein the gasket has a hole therein the size of the die through which the die protrudes.
- 11. The assembly according to claim 1, wherein the gasket has a shielding effectiveness to protect the die from at least 4 kV of electrostatic discharge pulse at a system level in which the assembly is to be used.
- 12. The assembly according to claim 1, wherein the gasket material has a shielding effectiveness of greater than 45 dB up to 3 GHz in frequency.
- 13. An apparatus for increasing the immunity of a microprocessor from electrostatic discharge events comprising:
 - a substrate;
 - a microprocessor mounted on the substrate;
- a thermal spreader in heat conducting relation with the microprocessor on a side of the microprocessor opposite the substrate;

a heat sink in heat conducting relation with the thermal spreader on a side of the thermal spreader opposite the microprocessor;

a gasket of a lossy material on the substrate surrounding the microprocessor to protect the microprocessor from electrostatic discharge pulses; and

wherein the thermal spreader extends beyond the outer peripheral edge of the microprocessor and overhangs an adjacent edge of the gasket.

- 14. The apparatus according to claim 13, wherein the lossy material of the gasket is a static dissipative material having a volume resistivity of greater than 10^2 ohm cm.
- 15. The apparatus according to claim 14, wherein the volume resistivity of the static dissipative material is less than 10⁹ ohm cm.
- 16. The apparatus according to claim 13, wherein the gasket is bonded to the substrate with an adhesive.

- 17. The apparatus according to claim 13, wherein the gasket is the size of the substrate.
- 18. The apparatus according to claim 13, wherein the gasket is formed of expanded polytetrafluorethylene filled with a conductive material to the extent that the gasket material has a volume resistivity of greater than 10² ohm cm.
- 19. The apparatus according to claim 13, wherein the gasket has a hole therein the size of the microprocessor through which the microprocessor protrudes.
- 20. The apparatus according to claim 13, wherein the gasket has a shielding effectiveness to protect the microprocessor from at least 4 kV of electrostatic discharge pulse at a system level in which the apparatus is to be used.
- 21. The apparatus according to claim 13, wherein the gasket material has a shielding effectiveness of greater than 45 dB up to 3 GHz in frequency.

- 22. An electronic package with protection from electrostatic discharge events comprising:
 - a substrate;
 - a semiconductor die mounted on the substrate;
- a heat sink in heat conducting relation with the semiconductor die on a side of the semiconductor die opposite the substrate; and
- a gasket of a lossy material on the substrate surrounding the semiconductor die to protect the die from electrostatic discharge pulses.
- 23. The electronic package according to claim 22, further comprising a thermal spreader located intermediate the semiconductor die and the heat sink to thermally couple the die and heat sink.
- 24. The electronic package according to claim 22, wherein the lossy material of the gasket is a static dissipative material having a volume resistivity of greater than 10^2 ohm cm.
- 25. The electronic package according to claim 22, wherein the gasket is formed of expanded polytetrafluorethylene filled with a conductive material to

the extent that the gasket material has a volume resistivity of greater than 10^2 ohm cm.

- 26. The electronic package according to claim 22, wherein the gasket has a hole therein the size of the die through which the die protrudes.
- 27. The electronic package according to claim 22, wherein the gasket has a shielding effectiveness to protect the die from at least 4 kV of electrostatic discharge pulse at a system level in which the electronic package is to be used.
- 28. The electronic package according to claim 22, wherein the gasket material has a shielding effectiveness of greater than 45 dB up to 3 GHz.
- 29. A method for increasing the immunity of a microprocessor from electrostatic discharge events comprising:

mounting a microprocessor on a substrate;

surrounding the microprocessor with a gasket formed of lossy, static dissipative material having a volume resistivity of greater than 10² ohm cm; and arranging a heat spreader in heat conducting relation with the

microprocessor and atop at least a portion of the gasket.

30. The method according to claim 29, further comprising adhesively bonding the gasket to the substrate.